

General Description

The ICS854S1208I is a low skew, 8 output LVDS Fanout Buffer with selectable divider. The ICS854S1208I has 2 selectable inputs that accept a variety of differential input types. The device provides the capability to suppress any glitch at the outputs of the device during an input clock switch to enhance clock redundancy in fault tolerant applications.

The divide select inputs, DIV_SELA and DIV_SELB, control the output frequency of each bank. The output banks can be independently selected for ÷1 or ÷2 operation. The output enable pins assigned to each output, support enabling and disabling each output individually.

The ICS854S1208I is characterized at full 3.3V or 2.5V output operating supply modes. Guaranteed output and part-to-part skew characteristics make the ICS854S1208I ideal for high performance applications.

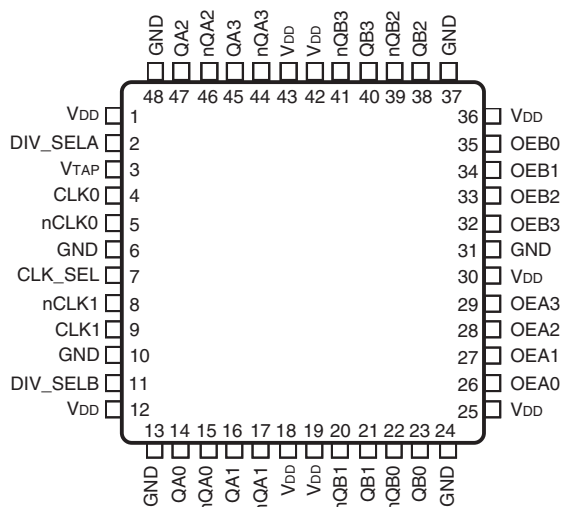
Features

- Eight differential LVDS output pairs
Each output has individual synchronous output enable
- Two selectable differential CLKx, nCLKx input pairs
- CLKx, nCLKx pairs can accept the following differential input levels: LVPECL, LVDS, HCSL
- Maximum output frequency: 1.5GHz
- Independent bank control for ÷1 or ÷2 operation
- Glitchless output behavior during input switch
- Output skew: 40ps (maximum)
- Bank skew: 35ps (maximum)
- Full 3.3V or 2.5V supply mode
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Supply Mode Operation Table

| 3.3V Operation | 2.5V Operation |
|--------------------------|-------------------------|
| V _{DD} = 3.3V | V _{DD} = 2.5V |
| V _{TAP} = Float | V _{TAP} = 2.5V |

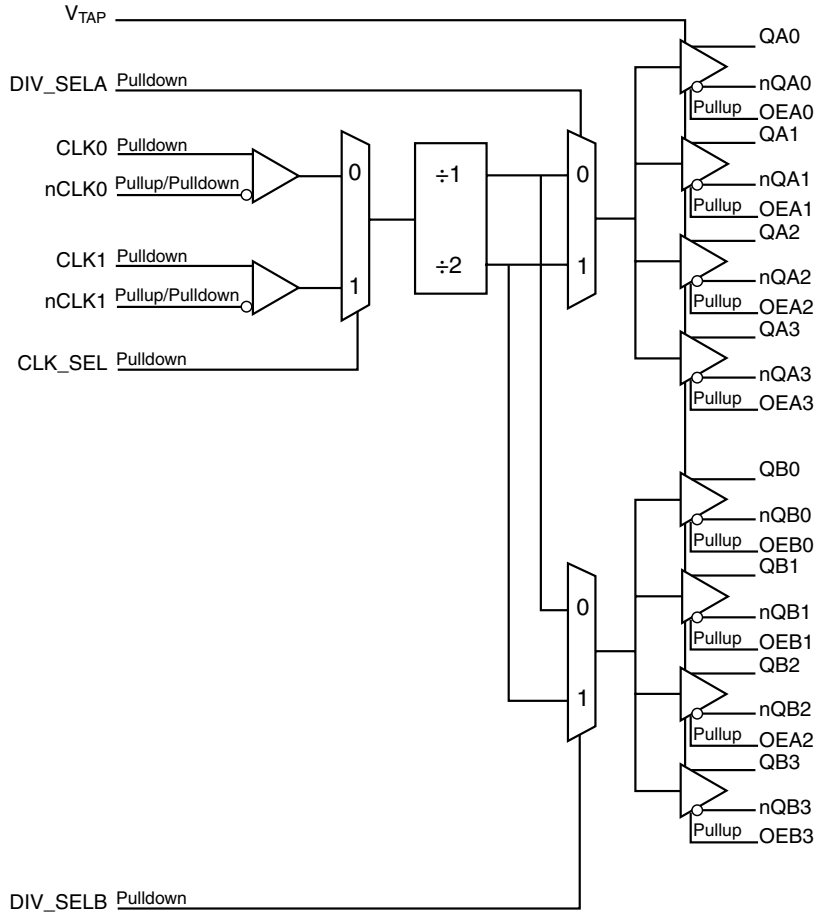
Pin Assignment



ICS854S1208I

48-Pin TQFP, E-Pad
7mm x 7mm x 1mm package body
Y Package
Top View

Block Diagram



Function Description

The ICS854S1208I has a glitch free input mux that is controlled by the CLK_SEL pin. It is designed to switch between 2 input clocks whether running or not. In the case where both clocks are running, when CLK_SEL changes, the output clocks go low after one cycle

of the output clock (nominally). The outputs then stay low for one cycle of the new input clock (nominally) and then begin to follow the new input clock. This is shown in *Figure 1A*.

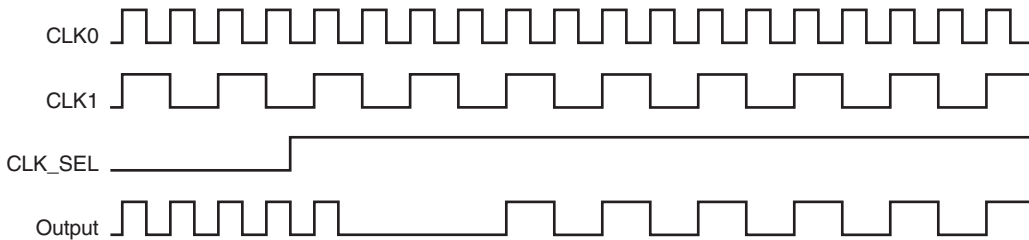


Figure 1A. CLK_SEL Timing Diagram

Another case is where one of the inputs was selected and running but has since stopped (either high or low). If a CLK_SEL event happens after a clock has stopped, the output change can take effect up to 1 μ s

after the input clock stopped. The output will go low and then follow the second period of the new clock input. Figure 1B shows an example of this.

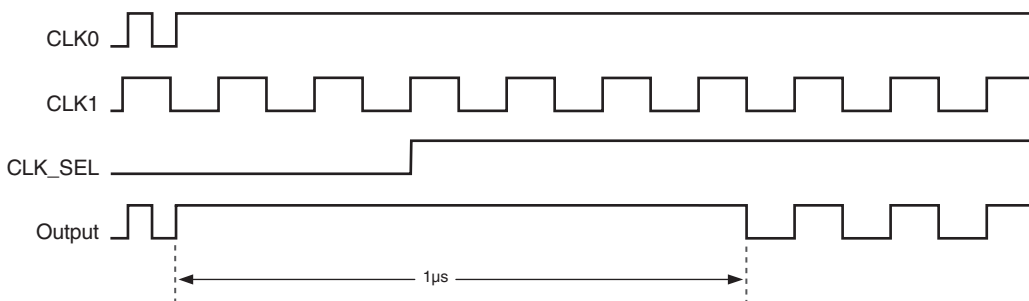


Figure 1B. CLK_SEL with Bad Input Timing Diagram

Table 1. Pin Descriptions

| Number | Name | Type | | Description |
|-----------------------------------|------------------|--------|---------------------|---|
| 1, 12, 18, 19, 25, 30, 36, 42, 43 | V _{DD} | Power | | Power supply pins. |
| 2 | DIV_SELA | Input | Pulldown | Controls frequency division for QA[0:3], nQA[0:3] outputs. LVCMOS / LVTTTL interface levels. |
| 3 | V _{TAP} | Power | | Power supply mode. See <i>Supply Mode Operation Table</i> on page 1. |
| 4 | CLK0 | Input | Pulldown | Non-inverting differential clock input. |
| 5 | nCLK0 | Input | Pullup/ Pulldown | Inverting differential clock input. V _{DD} /2 default when left floating. |
| 6, 10, 13, 24, 31, 37, 48 | GND | Power | | Power supply ground. |
| 7 | CLK_SEL | Input | Pulldown | Clock select input. When HIGH, selects CLK1/nCLK1 inputs. When LOW, selects CLK0, nCLK0 inputs. LVCMOS / LVTTTL interface levels. |
| 8 | nCLK1 | Input | Pullup/ Pulldown | Inverting differential clock input. V _{DD} /2 default when left floating. |
| 9 | CLK1 | Input | Pulldown | Non-inverting differential clock input. |
| 11 | DIV_SELB | Input | Pulldown | Controls frequency division for QB[0:3], nQB[0:3] outputs. LVCMOS / LVTTTL interface levels. |
| 14, 15 | QA0, nQA0 | Output | | Differential output pair. LVDS interface levels. |
| 16, 17 | QA1, nQA1 | Output | | Differential output pair. LVDS interface levels. |
| 20, 21 | nQB1, QB1 | Output | | Differential output pair. LVDS interface levels. |
| 22, 23 | nQB0, QB0 | Output | | Differential output pair. LVDS interface levels. |
| 26 | OEA0 | Input | Pullup | Output enable for QA0 output pair. LVCMOS/LVTTTL interface levels. See Table 3A. |
| 27 | OEA1 | Input | Pullup | Output enable for QA1 output pair. LVCMOS/LVTTTL interface levels. See Table 3A. |
| 28 | OEA2 | Input | Pullup | Output enable for QA2 output pair. LVCMOS/LVTTTL interface levels. See Table 3A. |
| 29 | OEA3 | Input | Pullup | Output enable for QA3 output pair. LVCMOS/LVTTTL interface levels. See Table 3A. |
| 32 | OEB3 | Input | Pullup | Output enable for QB3 output pair. LVCMOS/LVTTTL interface levels. See Table 3B. |
| 33 | OEB2 | Input | Pullup | Output enable for QB2 output pair. LVCMOS/LVTTTL interface levels. See Table 3B. |
| 34 | OEB1 | Input | Pullup | Output enable for QB1 output pair. LVCMOS/LVTTTL interface levels. See Table 3B. |
| 35 | OEB0 | Input | Pullup | Output enable for QB0 output pair. LVCMOS/LVTTTL interface levels. See Table 3B. |
| 38, 39 | QB2, nQB2 | Output | | Differential output pair. LVDS interface levels. |
| 40, 41 | QB3, nQB3 | Output | | Differential output pair. LVDS interface levels. |
| 44, 45 | nQA3, QA3 | Output | | Differential output pair. LVDS interface levels. |
| 46, 47 | nQA2, QA2 | Output | | Differential output pair. LVDS interface levels. |

NOTE: *Pullup and Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|-------------------------|-----------------|---------|---------|---------|-------|
| C _{IN} | Input Capacitance | | | 2 | | pF |
| R _{PULLUP} | Input Pullup Resistor | | | 51 | | kΩ |
| R _{PULLDOWN} | Input Pulldown Resistor | | | 51 | | kΩ |

Function Tables**Table 3A. OEAx Function Table**

| Inputs | Outputs | |
|-------------|---------|----------|
| | QA[0:3] | nQA[0:3] |
| 0 | LOW | HIGH |
| 1 (default) | Active | Active |

Table 3B. OEEx Function Table

| Inputs | Outputs | |
|-------------|---------|----------|
| | QB[0:3] | nQB[0:3] |
| 0 | LOW | HIGH |
| 1 (default) | Active | Active |

Table 3C. DIV_SELA Function Table

| Input | Frequency Division |
|-------------|--------------------|
| DIV_SELA | |
| 0 (default) | ÷1 |
| 1 | ÷2 |

Table 3D. DIV_SELB Function Table

| Input | Frequency Division |
|-------------|--------------------|
| DIV_SELB | |
| 0 (default) | ÷1 |
| 1 | ÷2 |

Table 3E. CLK_SEL Function Table

| Input | Input Selection |
|-------------|-----------------|
| CLK_SEL | |
| 0 (default) | CLK0, nCLK0 |
| 1 | CLK1, nCLK1 |

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item | Rating |
|--|--------------------------|
| Supply Voltage, V_{DD} | 4.6V |
| Inputs, V_I | -0.5V to $V_{DD} + 0.5V$ |
| Outputs, V_O | -0.5V to $V_{DD} + 0.5V$ |
| Package Thermal Impedance, θ_{JA} | 33.1°C/W (0 mps) |
| Storage Temperature, T_{STG} | -65°C to 150°C |

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-------------------------|-----------------|---------|---------|---------|-------|
| V_{DD} | Positive Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{TAP} | Power Supply Mode | | Float | | | V |
| I_{DD} | Power Supply Current | | | | 305 | mA |

Table 4B. Power Supply DC Characteristics, $V_{DD} = V_{TAP} = 2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-------------------------|-----------------|---------|---------|---------|-------|
| V_{DD} | Positive Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| V_{TAP} | Positive Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| I_{DD} | Power Supply Current | | | | 290 | mA |
| I_{TAP} | Power Supply Current | | | | 2.2 | mA |

Table 4C. LVCMOS/LVTTL DC Characteristics, $V_{DD} = 3.3V \pm 5\%$ or $V_{DD} = V_{TAP} = 2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|--------------------|---|---------|---------|----------------|---------|
| V_{IH} | Input High Voltage | $V_{DD} = 3.465V$ | 2.2 | | $V_{DD} + 0.3$ | V |
| | | $V_{DD} = 2.625V$ | 1.7 | | $V_{DD} + 0.3$ | V |
| V_{IL} | Input Low Voltage | $V_{DD} = 3.465V$ | -0.3 | | 0.8 | V |
| | | $V_{DD} = 2.625V$ | -0.3 | | 0.7 | V |
| I_{IH} | Input High Current | DIV_SELx, CLK_SEL $V_{DD} = V_{IN} = 3.465V$ or $2.625V$ | | | 150 | μA |
| | | OEA[3:0], OEB[3:0] $V_{DD} = V_{IN} = 3.465V$ or $2.625V$ | | | 10 | μA |
| I_{IL} | Input Low Current | DIV_SELx, CLK_SEL $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -10 | | | μA |
| | | OEA[3:0], OEB[3:0] $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -150 | | | μA |

Table 4D. Differential DC Characteristics, $V_{DD} = 3.3V \pm 5\%$ or $V_{DD} = V_{TAP} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|--------------------------------------|-----------------------------|--|---------|-----------------|---------------|
| I_{IH} | Input High Current | CLK0, CLK1, nCLK0, nCLK1 | $V_{DD} = V_{IN} = 3.465V$ or $2.625V$ | | 150 | μA |
| I_{IL} | Input Low Current | CLK0, CLK1 | $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -10 | | μA |
| | | nCLK0, nCLK1 | $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -150 | | μA |
| V_{PP} | Peak-to-Peak Voltage; NOTE 1 | | 0.15 | | 1.3 | V |
| V_{CMR} | Common Mode Input Voltage; NOTE 1, 2 | | GND + 0.5 | | $V_{DD} - 0.85$ | V |

NOTE 1: V_{IL} should not be less than $-0.3V$.NOTE 2: Common mode input voltage is defined as V_{IH} .**Table 4E. LVDS DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C**

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|-----------------------------|-----------------|---------|---------|---------|-------|
| V_{OD} | Differential Output Voltage | | 247 | | 454 | mV |
| ΔV_{OD} | V_{OD} Magnitude Change | | | | 50 | mV |
| V_{OS} | Offset Voltage | | 1.2 | | 1.47 | V |
| ΔV_{OS} | V_{OS} Magnitude Change | | | | 50 | mV |

Table 4F. LVDS DC Characteristics, $V_{DD} = V_{TAP} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|-----------------------------|-----------------|---------|---------|---------|-------|
| V_{OD} | Differential Output Voltage | | 247 | | 454 | mV |
| ΔV_{OD} | V_{OD} Magnitude Change | | | | 50 | mV |
| V_{OS} | Offset Voltage | | 1.15 | | 1.45 | V |
| ΔV_{OS} | V_{OS} Magnitude Change | | | | 50 | mV |

AC Electrical Characteristics

Table 5A. AC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|--------------|------------------------------|------------------------|---------|---------|---------|-------|
| f_{OUT} | Output Frequency | | | | 1.5 | GHz |
| t_{PD} | Propagation Delay; NOTE 1 | | 0.7 | | 1.75 | ns |
| $t_{sk(o)}$ | Output Skew; NOTE 2, 3 | | | | 40 | ps |
| $t_{sk(pp)}$ | Part-to-Part Skew; NOTE 3, 4 | | | | 400 | ps |
| $t_{sk(b)}$ | Bank Skew; NOTE 3, 5 | | | | 35 | ps |
| t_R / t_F | Output Rise/Fall Time | 20% to 80% | 55 | | 250 | ps |
| odc | Output Duty Cycle | $f \leq 750\text{MHz}$ | 44 | | 56 | % |
| t_{EN} | Output Enable Time; NOTE 6 | | | | 10 | ns |
| t_{DIS} | Output Disable Time; NOTE 6 | | | | 10 | ns |

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: Measured from the differential input crossing point to the differential cross points.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the differential cross points.

NOTE 3: These parameters are guaranteed by characterization. Not tested in production.

NOTE 4: Defined as skew between outputs on different devices operating at the same supply voltage, same temperature and with equal load conditions. Using the same type of input on each device, the output is measured at the differential cross points.

NOTE 5: Defined as skew within a bank of outputs at the same supply voltage and with equal load conditions.

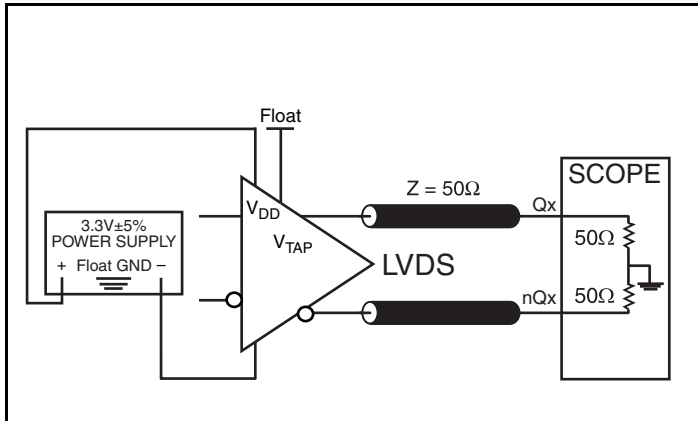
NOTE 6: These parameters are guaranteed by characterization. Not tested in production.

Table 5B. AC Characteristics, $V_{DD} = V_{TAP} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

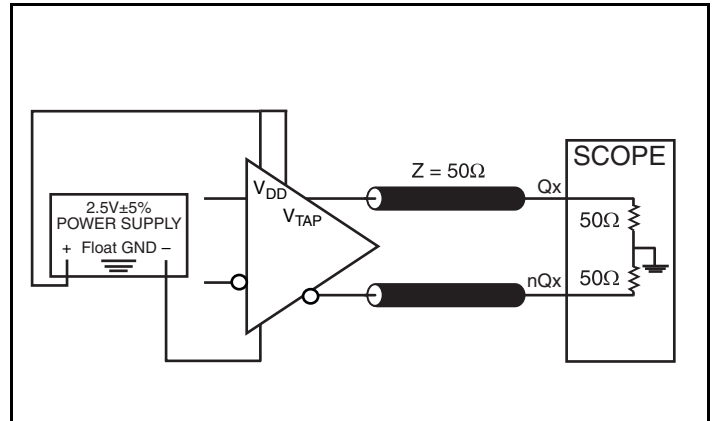
| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|--------------|------------------------------|------------------------|---------|---------|---------|-------|
| f_{OUT} | Output Frequency | | | | 1.5 | GHz |
| t_{PD} | Propagation Delay; NOTE 1 | | 0.6 | | 1.8 | ns |
| $t_{sk(o)}$ | Output Skew; NOTE 2, 3 | | | | 40 | ps |
| $t_{sk(pp)}$ | Part-to-Part Skew; NOTE 3, 4 | | | | 400 | ps |
| $t_{sk(b)}$ | Bank Skew; NOTE 3, 5 | | | | 35 | ps |
| t_R / t_F | Output Rise/Fall Time | 20% to 80% | 50 | | 275 | ps |
| odc | Output Duty Cycle | $f \leq 750\text{MHz}$ | 44 | | 56 | % |
| t_{EN} | Output Enable Time; NOTE 6 | | | | 10 | ns |
| t_{DIS} | Output Disable Time; NOTE 6 | | | | 10 | ns |

For NOTES, see Table 5A above.

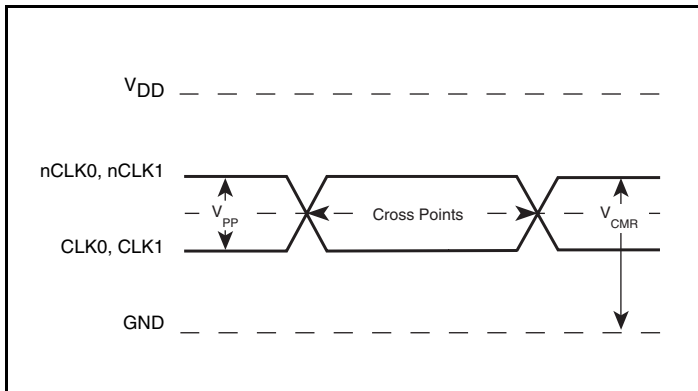
Parameter Measurement Information



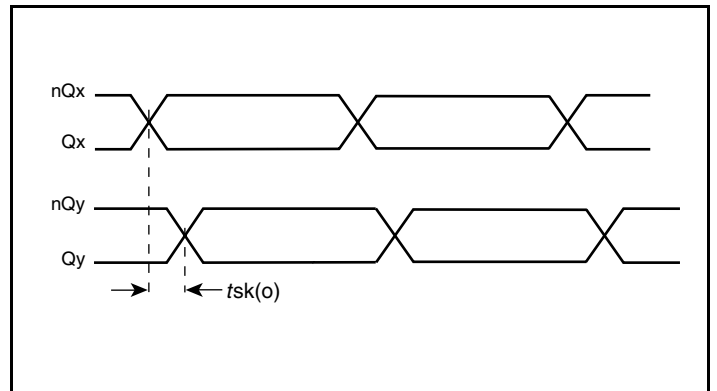
3.3V LVDS Output Load AC Test Circuit



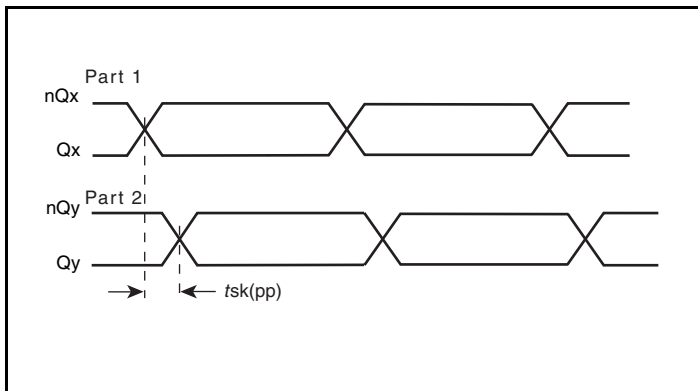
2.5V LVDS Output Load AC Test Circuit



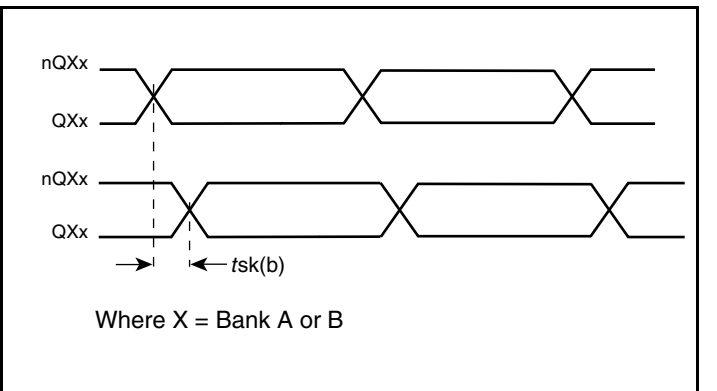
Differential Input Level



Output Skew

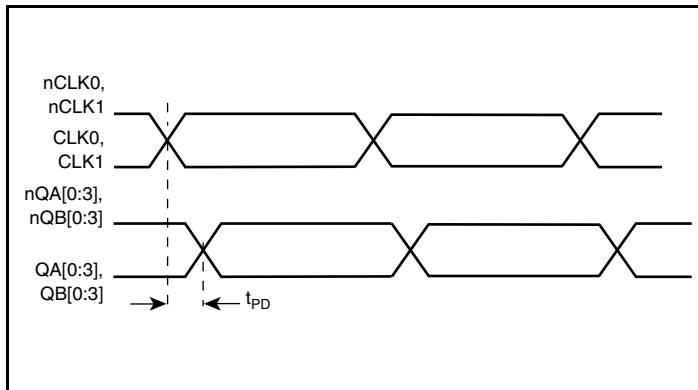


Part-to-Part Skew

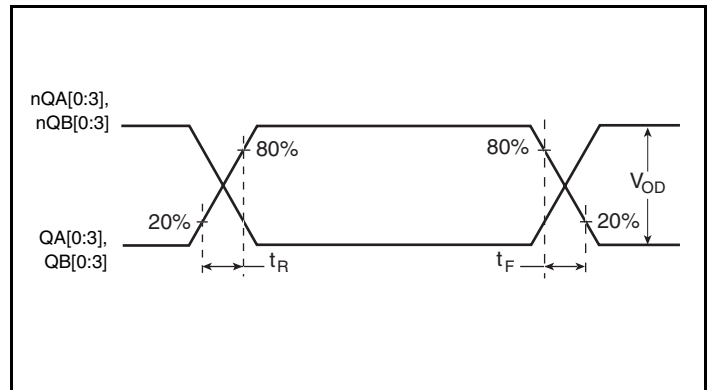


Bank Skew

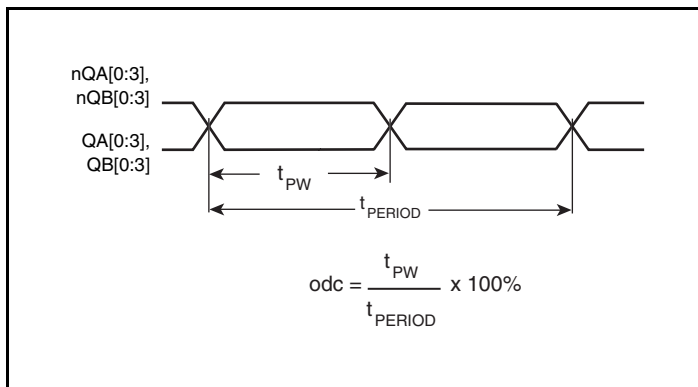
Parameter Measurement Information, continued



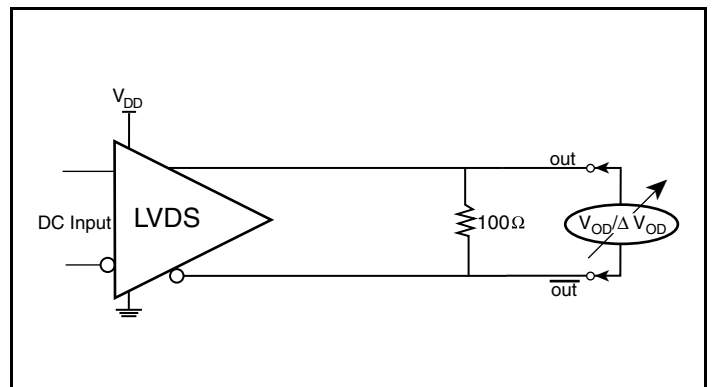
Propagation Delay



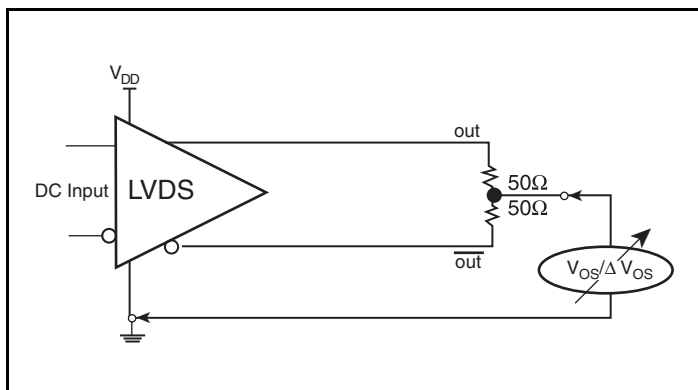
Output Rise/Fall Time



Output Duty Cycle/Pulse Width/Period



Differential Output Voltage Setup



Offset Voltage Setup

Applications Information

Wiring the Differential Input to Accept Single-Ended Levels

Figure 2 shows how a differential input can be wired to accept single ended levels. The reference voltage $V_1 = V_{DD}/2$ is generated by the bias resistors R1 and R2. The bypass capacitor (C1) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of R1 and R2 might need to be adjusted to position the V_1 in the center of the input voltage swing. For example, if the input clock swing is 2.5V and $V_{DD} = 3.3V$, R1 and R2 value should be adjusted to set V_1 at 1.25V. The values below are for when both the single ended swing and V_{DD} are at the same voltage. This configuration requires that the sum of the output impedance of the driver (R_o) and the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways. First, R3 and R4 in parallel should equal the transmission line

impedance. For most 50Ω applications, R3 and R4 can be 100Ω. The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver. When using single-ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full rail LVCMOS signaling, it is recommended that the amplitude be reduced. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however V_{IL} cannot be less than $-0.3V$ and V_{IH} cannot be more than $V_{DD} + 0.3V$. Though some of the recommended components might not be used, the pads should be placed in the layout. They can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a differential signal.

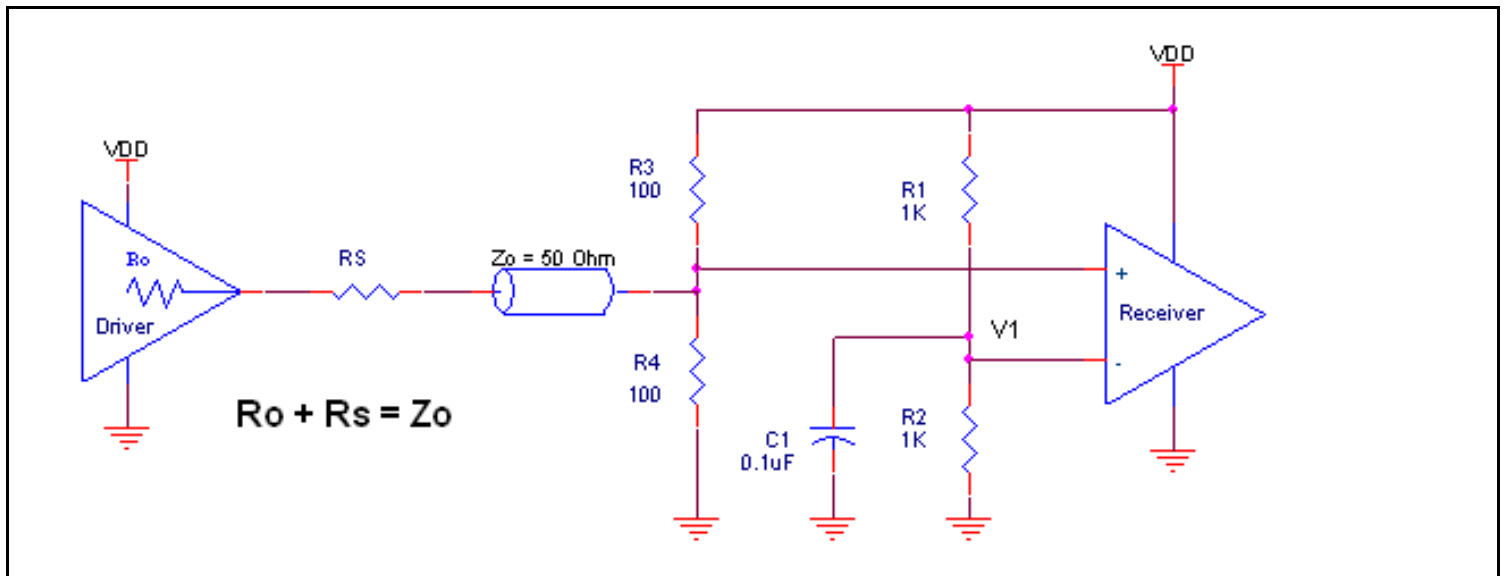


Figure 2. Recommended Schematic for Wiring a Differential Input to Accept Single-ended Levels

Recommendations for Unused Input and Output Pins

Inputs:

CLK/nCLK Inputs

For applications requiring only one differential input, the unused CLK and nCLK input can be left floating. Though not required, but for additional protection, a 1kΩ resistor can be tied from CLK pin to ground.

LVCMOS Control Pins

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

Outputs:

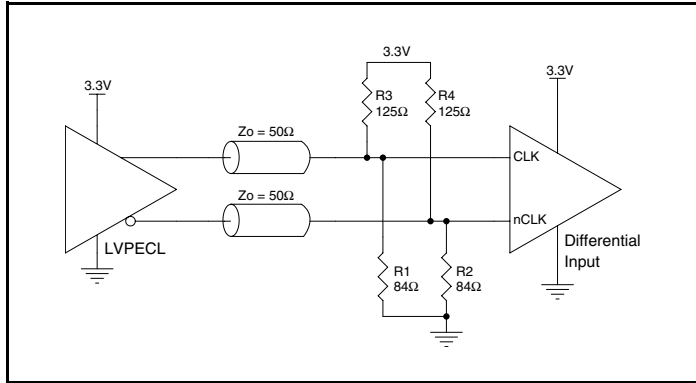
LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating, there should be no trace attached

3.3V Differential Clock Input Interface

The CLK /nCLK accepts LVDS, LVPEACL, HCSL and other differential signals. Both signals must meet the V_{PP} and V_{CMR} input requirements. *Figures 3A to 3D* show interface examples for the CLK/nCLK input driven by the most common driver types. The input

interfaces suggested here are examples only. Please consult with the vendor of the driver component to confirm the driver termination requirements.



3A. CLK/nCLK Input Driven by a 3.3V LVPEACL Driver

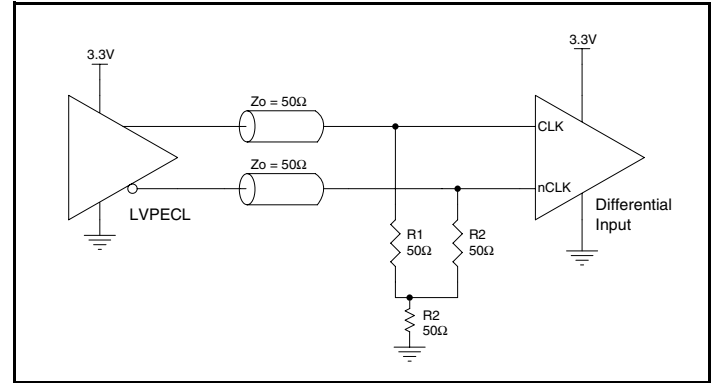


Figure 3B. CLK/nCLK Input Driven by a 3.3V LVPEACL Driver

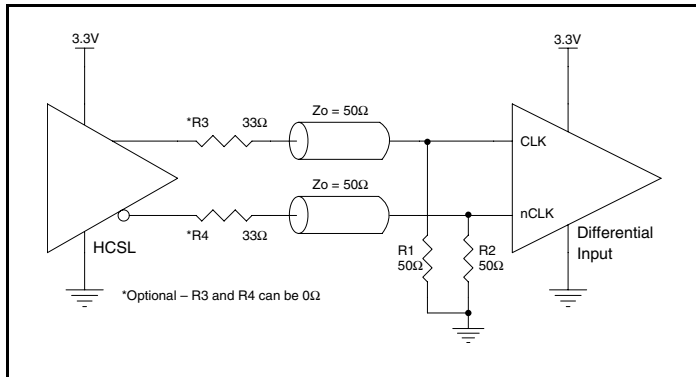


Figure 3C. CLK/nCLK Input Driven by a 3.3V HCSL Driver

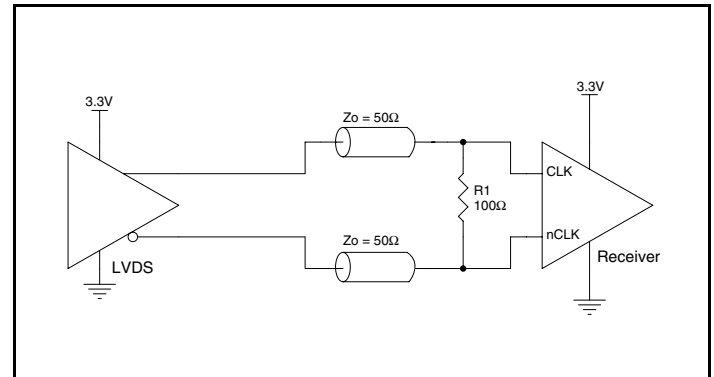


Figure 3D. CLK/nCLK Input Driven by a 3.3V LVDS Driver

2.5V Differential Clock Input Interface

The CLK /nCLK accepts LVDS, LVPECL, HCSL and other differential signals. Both signals must meet the V_{PP} and V_{CMR} input requirements. *Figures 4A to 4D* show interface examples for the CLK/nCLK input driven by the most common driver types. The input

interfaces suggested here are examples only. Please consult with the vendor of the driver component to confirm the driver termination requirements.

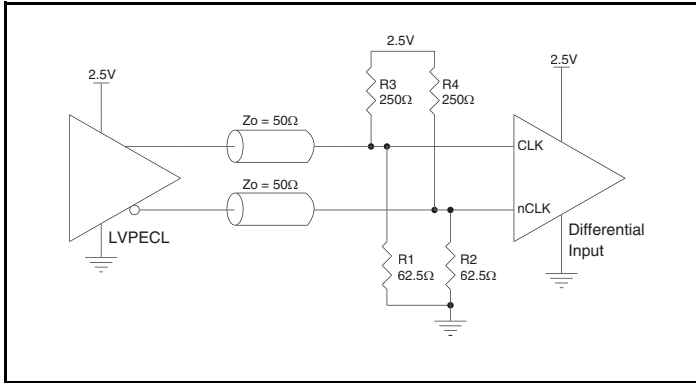


Figure 4A. CLK/nCLK Input Driven by a 2.5V LVPECL Driver

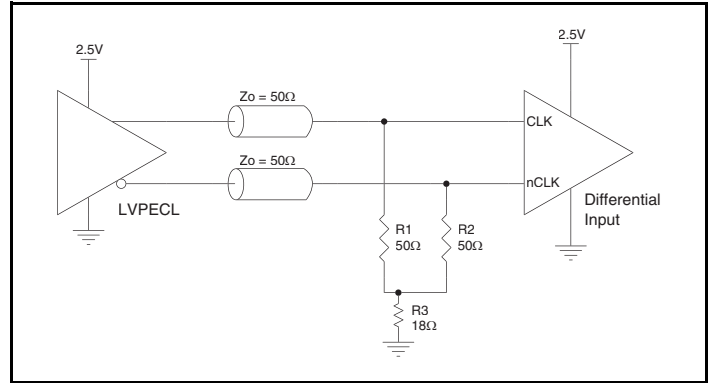


Figure 4B. CLK/nCLK Input Driven by a 2.5V LVPECL Driver

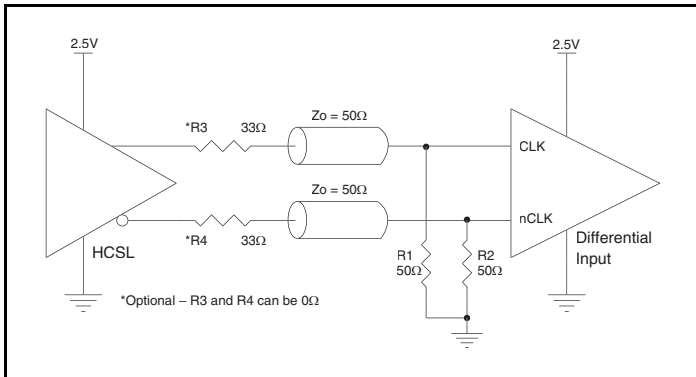


Figure 4C. CLK/nCLK Input Driven by a 2.5V HCSL Driver

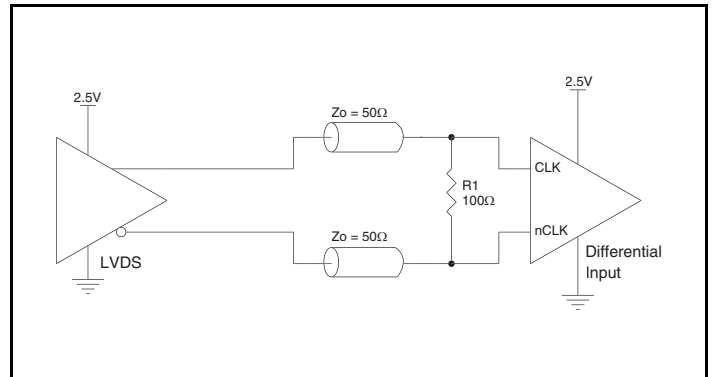
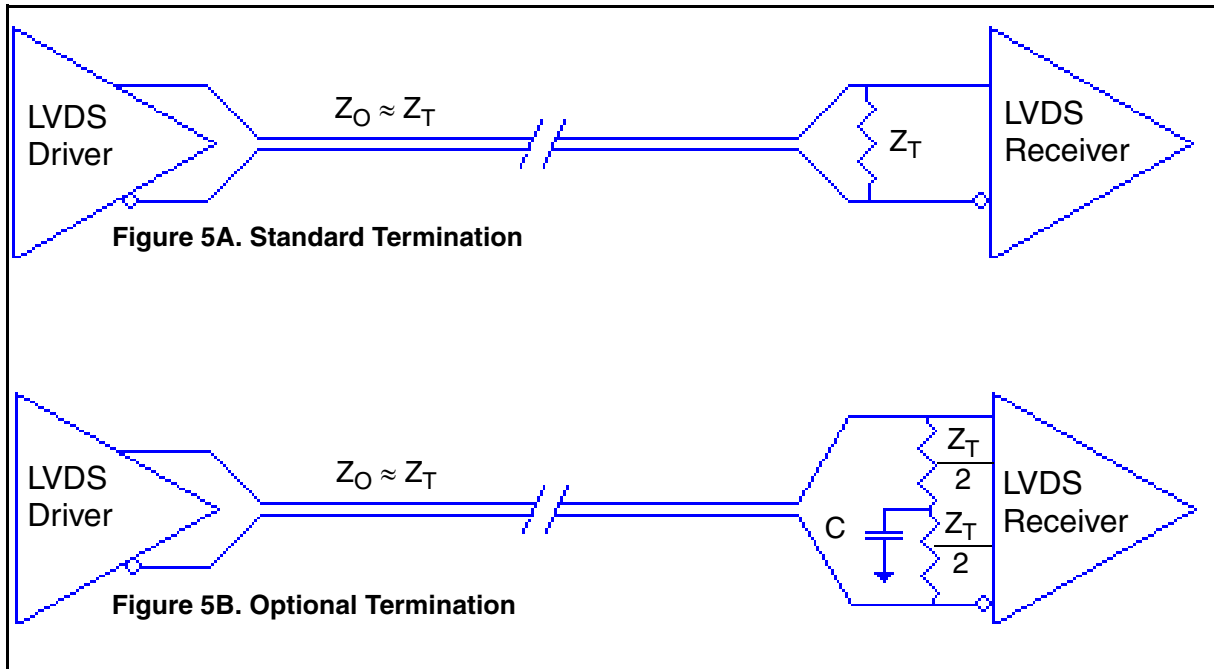


Figure 4D. CLK/nCLK Input Driven by a 2.5V LVDS Driver

LVDS Driver Termination

A general LVDS interface is shown in *Figure 5A*. Standard termination for LVDS type output structure requires both a 100Ω parallel resistor at the receiver and a 100Ω differential transmission line environment. In order to avoid any transmission line reflection issues, the 100Ω resistor must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The

standard termination schematic as shown in *Figure 5A* can be used with either type of output structure. If using a non-standard termination, it is recommended to contact IDT and confirm if the output is a current source or a voltage source type structure. In addition, since these outputs are LVDS compatible, the amplitude and common mode input range of the input receivers should be verified for compatibility with the output.



LVDS Driver Termination

LVDS Power Considerations

This section provides information on power dissipation and junction temperature for the ICS854S1208I. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS854S1208I is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

Max power dissipation occurs at $-40^{\circ}C$.

Max I_{DD} at $-40^{\circ}C = 305mA$

- $Power_{MAX} = V_{DD_MAX} * I_{DD_MAX} = 3.465V * 305mA = \mathbf{1056.825mW}$

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is $125^{\circ}C$. Limiting the internal transistor junction temperature, T_j , to $125^{\circ}C$ ensures that the bond wire and bond pad temperature remains below $125^{\circ}C$.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is $33.1^{\circ}C/W$ per Table 6 below.

Max I_{DD} at $85^{\circ}C = 287.8mA$.

Max power at $85^{\circ}C = 3.465V * 287.8mA = 997.227mW$.

Therefore, T_j for an ambient temperature of $85^{\circ}C$ with all outputs switching is:

$$85^{\circ}C + 0.997W * 33.1^{\circ}C/W = 118^{\circ}C. \text{ This is below the limit of } 125^{\circ}C.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 6. Thermal Resistance θ_{JA} for 48 Lead TQFP, E-Pad, Forced Convection

| Meters per Second | θ_{JA} by Velocity | | |
|---|---------------------------|-------------------|-------------------|
| | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | $33.1^{\circ}C/W$ | $27.2^{\circ}C/W$ | $25.7^{\circ}C/W$ |

Reliability Information

Table 7. θ_{JA} vs. Air Flow Table for a 48 Lead TQFP, E-Pad

| θ_{JA} vs. Air Flow | | | |
|---|----------|----------|----------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 33.1°C/W | 27.2°C/W | 25.7°C/W |

Transistor Count

The transistor count for ICS854S1208I is: 9878

Package Outline and Package Dimensions

Package Outline - Y Suffix for 48 Lead TQFP, E-Pad

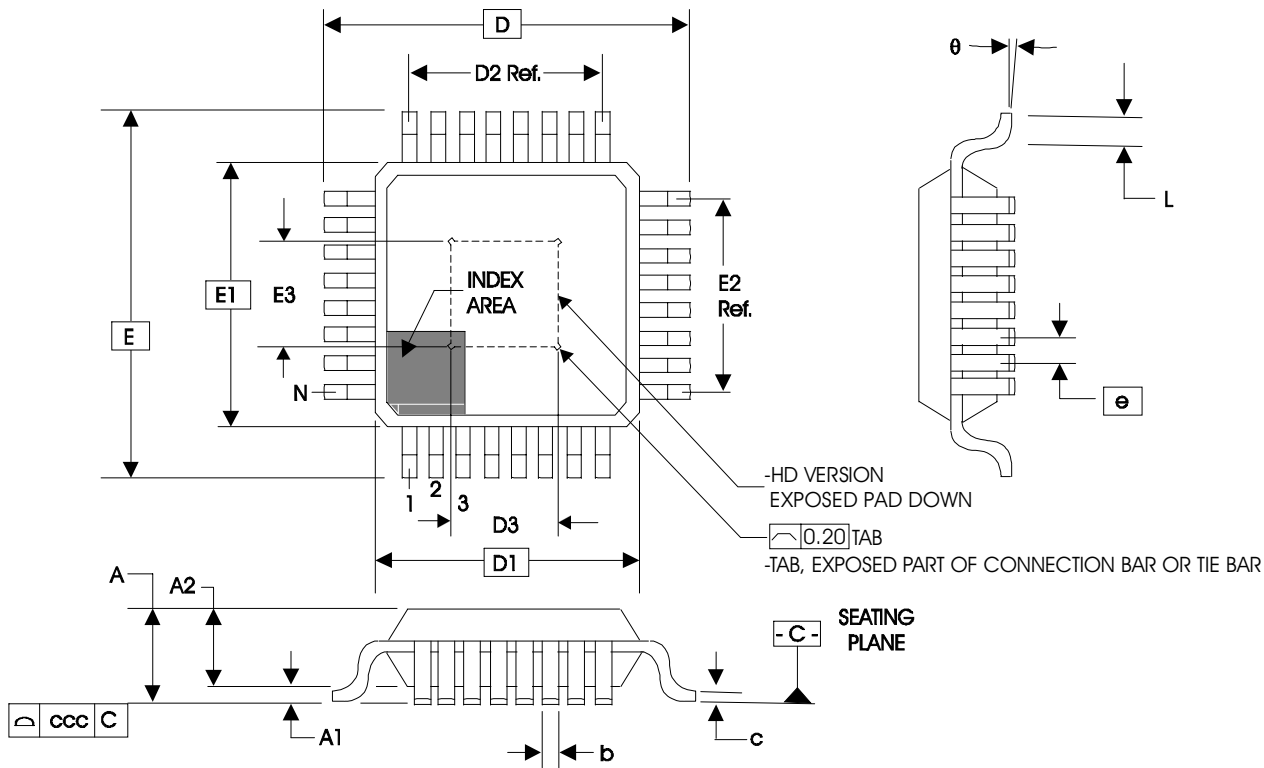


Table 8. Package Dimensions for 48 Lead TQFP, E-Pad

| JEDEC Variation: BBC - HD | | | |
|-------------------------------|---------|------------|---------|
| All Dimensions in Millimeters | | | |
| Symbol | Minimum | Nominal | Maximum |
| N | | 48 | |
| A | | | 1.20 |
| A1 | 0.05 | 0.10 | 0.15 |
| A2 | 0.95 | 1.00 | 1.05 |
| b | 0.17 | 0.22 | 0.27 |
| c | 0.09 | | 0.20 |
| D & E | | 9.00 Basic | |
| D1 & E1 | | 7.00 Basic | |
| D2 & E2 | | 5.50 Ref. | |
| D3 & E3 | | 3.5 | |
| e | | 0.5 Basic | |
| L | 0.45 | 0.60 | 0.75 |
| ccc | | | 0.08 |
| θ | 0° | | 7° |

Reference Document: JEDEC Publication 95, MS-026

Ordering Information

Table 9. Ordering Information

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|-------------------|--------------|---------------------------------|--------------------|---------------|
| 854S1208AYILF | ICS4S1208AIL | "Lead-Free" 48 Lead TQFP, E-Pad | Tray | -40°C to 85°C |
| 854S1208AYILFT | ICS4S1208AIL | "Lead-Free" 48 Lead TQFP, E-Pad | 1000 Tape & Reel | -40°C to 85°C |

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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